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March 2015



FGH60N60SF 600 V, 60 A Field Stop IGBT

Features

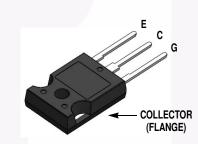
- High Current Capability
- Low Saturation Voltage: V_{CE(sat)} = 2.3 V @ I_C = 60 A
- High Input Impedance
- Fast Switching
- RoHS Compliant

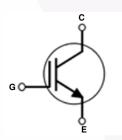
Applications

• Solar Inverter, UPS, Welder, PFC

General Description

Using novel field stop IGBT technology, Fairchild's field stop IGBTs offer the optimum performance for solar inverter, UPS, welder and PFC applications where low conduction and switching losses are essential.





Absolute Maximum Ratings

Symbol	Description		Ratings	Unit V	
V _{CES}	Collector to Emitter Voltage	600			
V _{GES}	Gate to Emitter Voltage	±20	V		
	Transient Gate-to-Emitter Voltage	±30	v		
I _C	Collector Current	@ T _C = 25°C	120	A	
	Collector Current	@ T _C = 100°C	60	A	
I _{CM (1)}	Pulsed Collector Current	@ T _C = 25°C	180	А	
P _D	Maximum Power Dissipation	@ T _C = 25°C	378	W	
	Maximum Power Dissipation	@ T _C = 100°C	151	W	
TJ	Operating Junction Temperature		-55 to +150	°C	
T _{stg}	Storage Temperature Range		-55 to +150	°C	
Τ _L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds	300	°C		

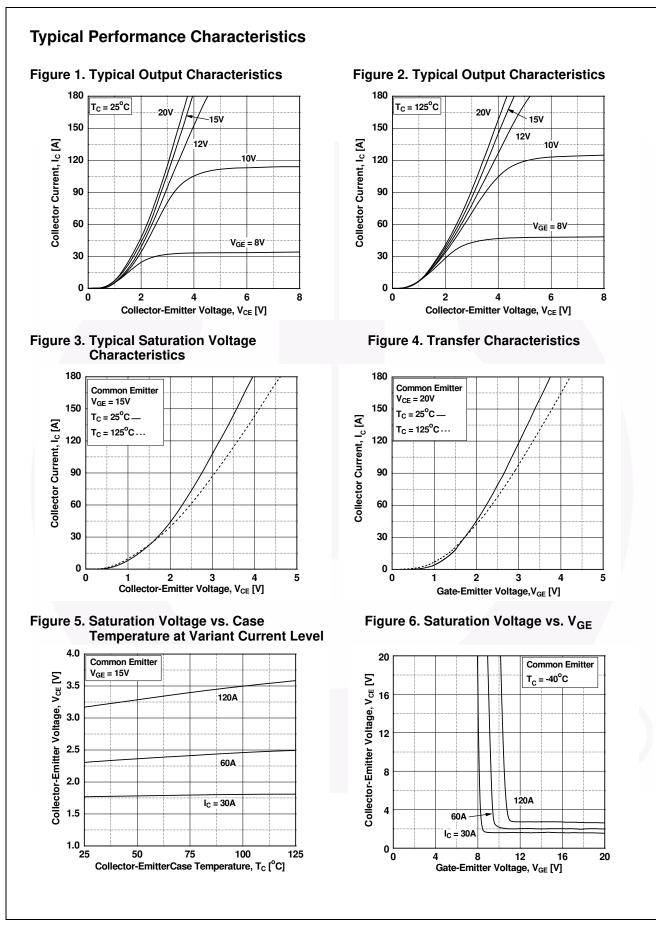
Notes:

1: Repetitive test, Pulse width limited by max. juntion temperature

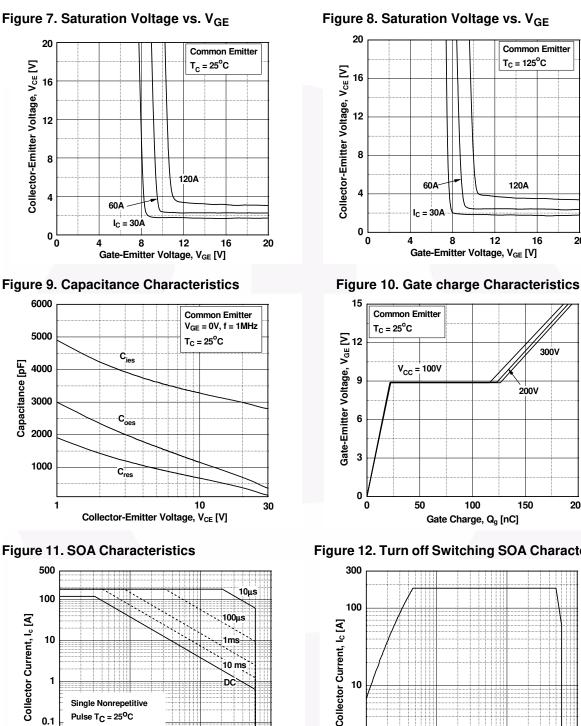
Thermal Characteristics

Symbol	Parameter	meter Typ.		Unit	
$R_{\theta JC}(IGBT)$	Thermal Resistance, Junction to Case	-	0.33	°C/W	
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient	-	40	°C/W	

Part Nu	Part NumberTop MarkPackageFGH60N60SFTUFGH60N60SFTO-247		Package	Packing Method	Reel Size	Tape Wid	th Q	Quantity	
FGH60N60			Tube	N/A	N/A		30		
Electric	al Ch	aracteristic	s of the I	GBT $T_{C} = 25^{\circ}C$ unless other	erwise noted				
Symbol	bol Parameter		Test Conditions		. Typ.	Max.	Unit		
Off Charac	teristics	1			H				
BV _{CES}	Collector to Emitter Breakdown Voltage		V _{GE} = 0 V, I _C = 250 μA 6		0 -	-	V		
$\Delta BV_{CES} / \Delta T_J$	Temperature Coefficient of Breakdown Voltage		$V_{GE} = 0 V, I_C = 250 \mu A$ -		0.4	-	V/ºC		
I _{CES}	Collector Cut-Off Current		V _{CE} = V _{CES} , V _{GE} = 0 V -		_	250	μA		
I _{GES}		akage Current		$V_{GE} = V_{GES}, V_{CE} = 0 V$	-	-	±400	nA	
On Charac	teristics	;							
V _{GE(th)}	G-E Th	reshold Voltage		$I_C = 250 \ \mu A, \ V_{CE} = V_{GE}$	4.	5.0	6.5	V	
		Collector to Emitter Saturation Voltage		$I_{C} = 60 \text{ A}, V_{GE} = 15 \text{ V}$	-	2.3	2.9	V	
V _{CE(sat)}	Collect			$I_{\rm C} = 60$ A, $V_{\rm GE} = 15$ V, $T_{\rm C} = 125^{\rm o}{\rm C}$		2.5	-	V	
Dynamic C	baracte	rietice							
C _{ies}	1	apacitance			-	2820	-	pF	
C _{oes}		Capacitance		$V_{CE} = 30 V, V_{GE} = 0 V,$	-	350	_	pF	
C _{res}		Reverse Transfer Capacitance		f = 1 MHz	-	140	-	pF	
Switching	1					00			
t _{d(on)}		n Delay Time	_	-	-	22	-	ns	
t _r	Rise Ti				-	42	-	ns	
t _{d(off)}		Turn-Off Delay Time		$V_{CC} = 400 \text{ V}, \text{ I}_{C} = 60 \text{ A},$ $R_{G} = 5 \Omega, \text{ V}_{GE} = 15 \text{ V},$		134	-	ns	
t _í	Fall Tin			nductive Load, $T_C = 25^{\circ}C$	°C -	31	62	ns	
E _{on}		n Switching Loss		-	-	1.79	-	mJ	
E _{off}		ff Switching Loss		-	-	0.67	-	mJ	
E _{ts}		witching Loss				2.46	-	mJ	
t _{d(on)}		n Delay Time		-	-	22	-	ns	
t _r	Rise Ti			+	-	44	-	ns	
t _{d(off)}		ff Delay Time		$V_{CC} = 400 \text{ V}, \text{ I}_{C} = 60 \text{ A}, \\ R_{G} = 5 \Omega, \text{ V}_{GE} = 15 \text{ V}, \\ \hline \text{Inductive Load, } T_{C} = 125^{\circ}\text{C}$		144	-	ns	
t _f	Fall Tin				5°C -	43	-	ns	
E _{on}		n Switching Loss			-	1.88	- /	mJ	
E _{off}		ff Switching Loss		1	-	1.0	-	mJ	
E _{ts}		witching Loss			-	2.88	-	mJ	
Qg		ate Charge		V _{CE} = 400 V, I _C = 60 A,	-	198	-	nC	
Q _{ge}		Emitter Charge		$V_{CE} = 400 \text{ V}, \text{ I}_{C} = 60 \text{ A},$ $V_{GE} = 15 \text{ V}$	-	22	-	nC	
Q _{gc}	Gate to	Collector Charge			-	106	-	nC	



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Typical Performance Characteristics

Figure 8. Saturation Voltage vs. V_{GE}

60A

I_C = 30A

8

Common Emitter

T_C = 125^oC

120A

16

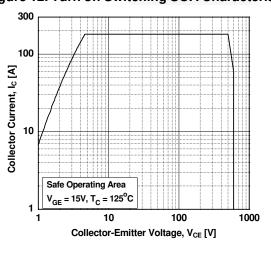
20

12

Gate-Emitter Voltage, V_{GE} [V]

Common Emitter $T_C = 25^{\circ}C$ 300V V_{CC} = 100V 2000 50 100 150 200 Gate Charge, Qg [nC]





0.01

1

Curves must be derated linearly with increase

10

Collector-Emitter Voltage, V_{CE} [V]

100

in temperature

1000

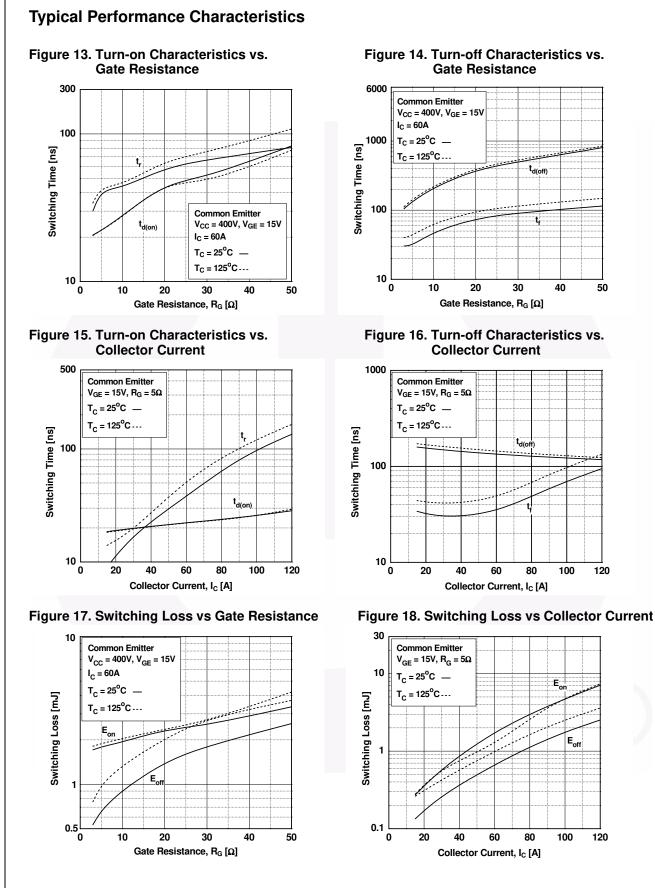


Figure 14. Turn-off Characteristics vs.

40

100

E,

E_{off}

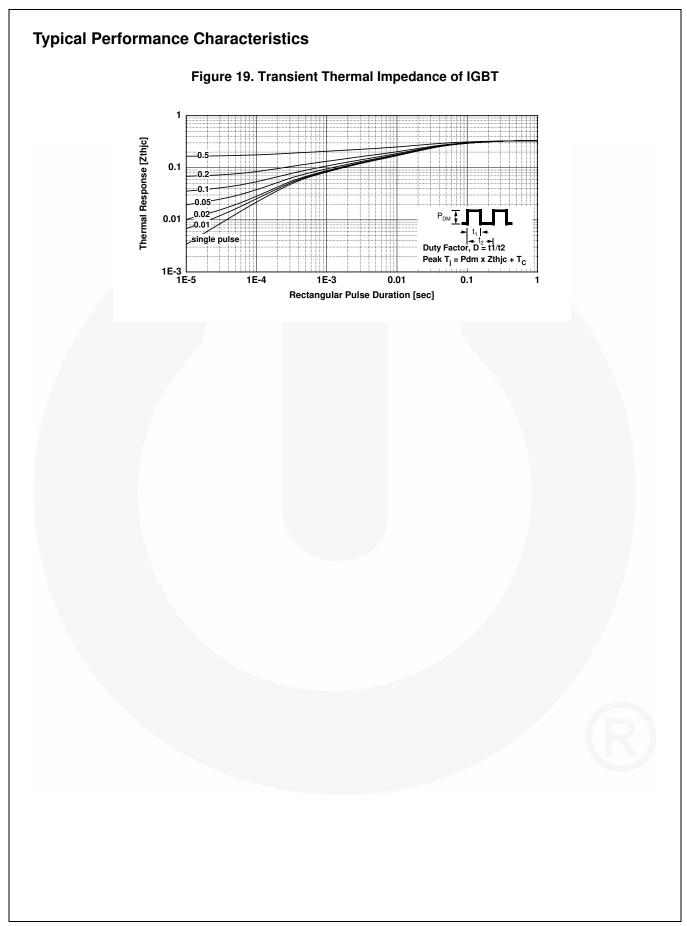
100

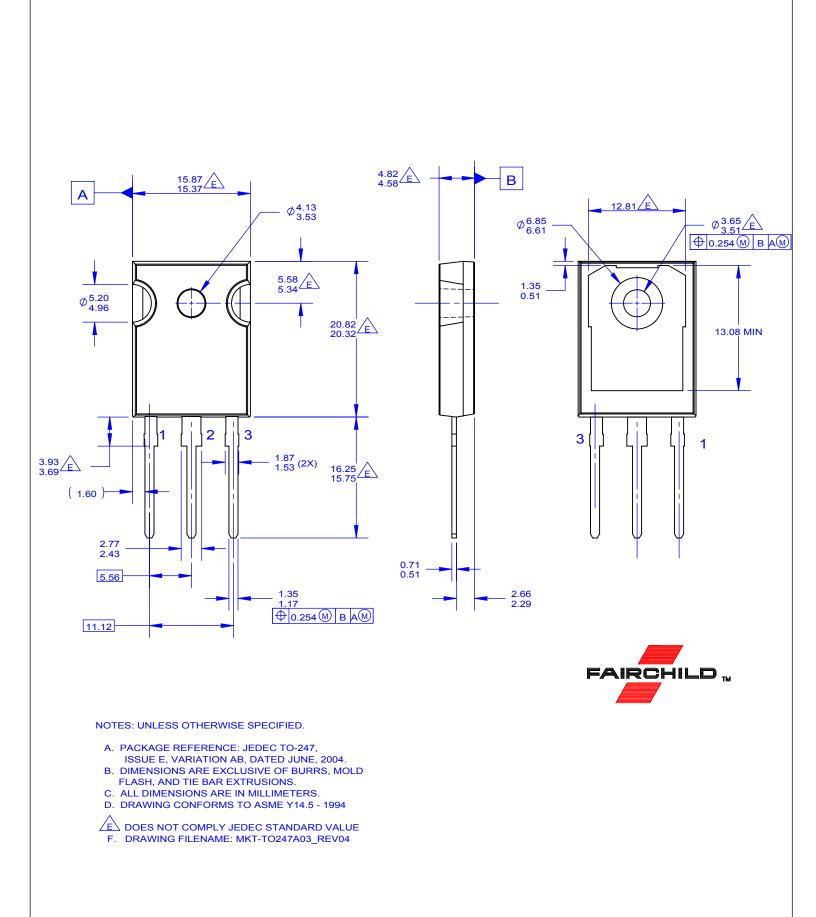
120

120

50

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